

# MC74LCX540

## Low-Voltage CMOS Octal Buffer Flow Through Pinout

### With 5 V-Tolerant Inputs and Outputs (3-State, Inverting)

The MC74LCX540 is a high performance, inverting octal buffer operating from a 2.3 to 3.6 V supply. This device is similar in function to the MC74LCX240, while providing flow through architecture. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A  $V_I$  specification of 5.5 V allows MC74LCX540 inputs to be safely driven from 5 V devices. The MC74LCX540 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable ( $\overline{OE1}$ ,  $\overline{OE2}$ ) inputs, when HIGH, disables the outputs by placing them in a HIGH Z condition.

#### Features

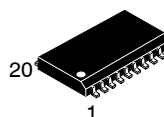
- Designed for 2.3 to 3.6 V  $V_{CC}$  Operation
- 5 V Tolerant – Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- $I_{OFF}$  Specification Guarantees High Impedance When  $V_{CC} = 0$  V
- LVTTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10  $\mu$ A)  
Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
  - ◆ Human Body Model >2000 V
  - ◆ Machine Model >200 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



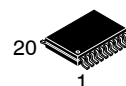
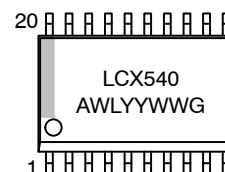
ON Semiconductor®

<http://onsemi.com>

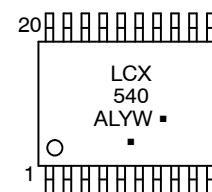
#### MARKING DIAGRAMS



SOIC-20 WB  
DW SUFFIX  
CASE 751D



TSSOP-20  
DT SUFFIX  
CASE 948E



A = Assembly Location  
L, WL = Wafer Lot  
Y, YY = Year  
W, WW = Work Week  
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

# MC74LCX540

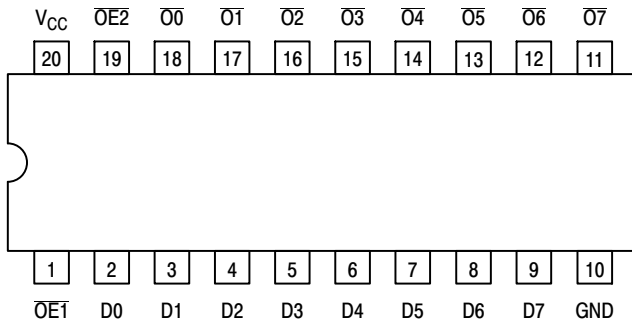


Figure 1. Pinout: 20-Lead (Top View)

## PIN NAMES

Pins	Function
$\overline{OE}_n$	Output Enable Inputs
Dn	Data Inputs
$\overline{O}_n$	3-State Outputs

## TRUTH TABLE

Inputs			Outputs
$\overline{OE}_1$	$\overline{OE}_2$	Dn	$\overline{O}_n$
L	L	L	H
L	L	H	L
X	H	X	Z
H	X	X	Z

H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State

X = High or Low Voltage Level and Transitions are Acceptable

For  $I_{CC}$  reasons, DO NOT FLOAT Inputs

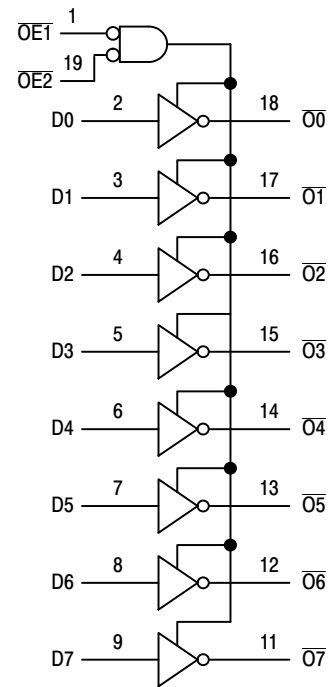


Figure 2. Logic Diagram

# MC74LCX540

## MAXIMUM RATINGS

Symbol	Parameter	Condition	Value	Units
$V_{CC}$	DC Supply Voltage		-0.5 to +7.0	V
$V_I$	DC Input Voltage		$-0.5 \leq V_I \leq +7.0$	V
$V_O$	DC Output Voltage	Output in 3-State	$-0.5 \leq V_O \leq +7.0$	V
		(Note 1)	$-0.5 \leq V_O \leq V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$V_I < GND$	-50	mA
$I_{OK}$	DC Output Diode Current	$V_O < GND$	-50	mA
		$V_O > V_{CC}$	+50	mA
$I_O$	DC Output Source/Sink Current		$\pm 50$	mA
$I_{CC}$	DC Supply Current Per Supply Pin		$\pm 100$	mA
$I_{GND}$	DC Ground Current Per Ground Pin		$\pm 100$	mA
$T_{STG}$	Storage Temperature Range		-65 to +150	°C
MSL	Moisture Sensitivity		Level 1	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Output in HIGH or LOW State.  $I_O$  absolute maximum rating must be observed.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Units
$V_{CC}$	Supply Voltage Operating Data Retention Only	2.0	3.3	3.6	V
		1.5	3.3	3.6	
$V_I$	Input Voltage	0		5.5	V
$V_O$	Output Voltage (HIGH or LOW State) (3-State)	0		$V_{CC}$	V
		0		5.5	
$I_{OH}$	HIGH Level Output Current, $V_{CC} = 3.0\text{ V} - 3.6\text{ V}$			-24	mA
$I_{OL}$	LOW Level Output Current, $V_{CC} = 3.0\text{ V} - 3.6\text{ V}$			24	mA
$I_{OH}$	HIGH Level Output Current, $V_{CC} = 2.7\text{ V} - 3.0\text{ V}$			-12	mA
$I_{OL}$	LOW Level Output Current, $V_{CC} = 2.7\text{ V} - 3.0\text{ V}$			12	mA
$T_A$	Operating Free-Air Temperature	-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, $V_{IN}$ from 0.8 V to 2.0 V, $V_{CC} = 3.0\text{ V}$	0		10	ns/V

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74LCX540DWR2G	SOIC-20 WB (Pb-Free)	1000 Tape & Reel
MC74LCX540DTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74LCX540DTR2G	TSSOP-20 (Pb-Free)	2000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MC74LCX540

## DC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Condition	T <sub>A</sub> = -40°C to +85°C		Units
			Min	Max	
V <sub>IH</sub>	HIGH Level Input Voltage (Note 2)	2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V	2.0		V
V <sub>IL</sub>	LOW Level Input Voltage (Note 2)	2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V		0.8	V
V <sub>OH</sub>	HIGH Level Output Voltage	2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V; I <sub>OH</sub> = -100 μA	V <sub>CC</sub> - 0.2		V
		V <sub>CC</sub> = 2.7 V; I <sub>OH</sub> = -12 mA	2.2		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -18 mA	2.4		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -24 mA	2.2		
V <sub>OL</sub>	LOW Level Output Voltage	2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V; I <sub>OL</sub> = 100 μA		0.2	V
		V <sub>CC</sub> = 2.7 V; I <sub>OL</sub> = 12 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 16 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 24 mA		0.55	
I <sub>OZ</sub>	3-State Output Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> , V <sub>OUT</sub> = 0 to 5.5 V		±5	μA
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>CC</sub> = 0, V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V		10	μA
I <sub>IN</sub>	Input Leakage Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 5.5 V or GND		±5	μA
I <sub>CC</sub>	Quiescent Supply Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 5.5 V or GND		10	μA
ΔI <sub>CC</sub>	Increase in I <sub>CC</sub> per Input	2.3 ≤ V <sub>CC</sub> ≤ 3.6 V; V <sub>IH</sub> = V <sub>CC</sub> - 0.6 V		500	μA

2. These values of V<sub>I</sub> are used to test DC electrical characteristics only.

## AC CHARACTERISTICS (t<sub>R</sub> = t<sub>F</sub> = 2.5 ns; C<sub>L</sub> = 50 pF; R<sub>L</sub> = 500 Ω)

Symbol	Parameter	Waveform	Limits			Units
			T <sub>A</sub> = -40°C to +85°C			
			V <sub>CC</sub> = 3.0 V to 3.6 V		V <sub>CC</sub> = 2.7 V	
			Min	Max	Max	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Input to Output	1	1.5	6.5	7.5	ns
			1.5	6.5	7.5	
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time to High and Low Level	2	1.5	8.5	9.5	ns
			1.5	8.5	9.5	
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time From High and Low Level	2	1.5	7.5	8.5	ns
			1.5	7.5	8.5	
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 3)			1.0		ns
				1.0		

3. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

## DYNAMIC SWITCHING CHARACTERISTICS

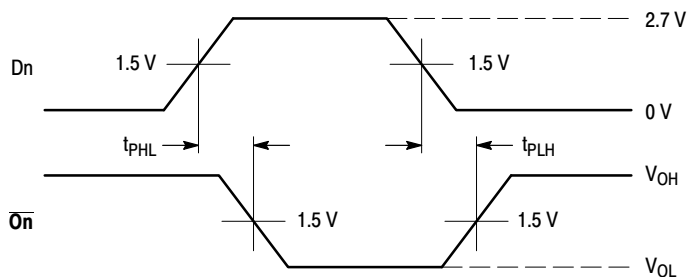
Symbol	Characteristic	Condition	T <sub>A</sub> = +25°C			Units
			Min	Typ	Max	
V <sub>OLP</sub>	Dynamic LOW Peak Voltage (Note 4)	V <sub>CC</sub> = 3.3 V, C <sub>L</sub> = 50 pF, V <sub>IH</sub> = 3.3 V, V <sub>IL</sub> = 0 V		0.8		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage (Note 4)	V <sub>CC</sub> = 3.3 V, C <sub>L</sub> = 50 pF, V <sub>IH</sub> = 3.3 V, V <sub>IL</sub> = 0 V		0.8		V

4. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

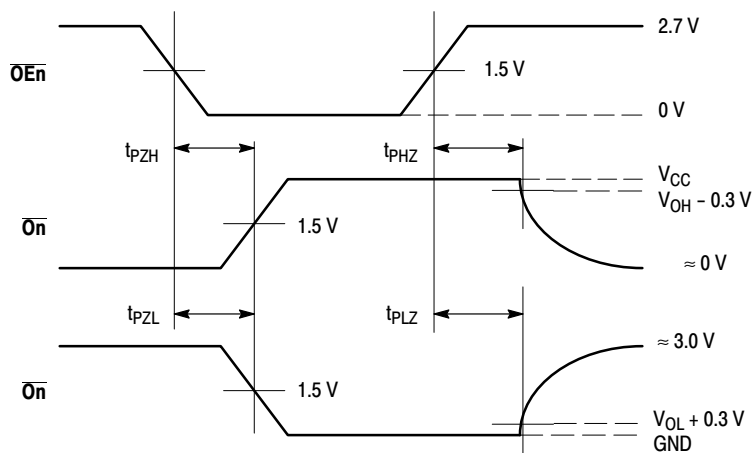
## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C <sub>IN</sub>	Input Capacitance	V <sub>CC</sub> = 3.3 V, V <sub>I</sub> = 0 V or V <sub>CC</sub>	7	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>CC</sub> = 3.3 V, V <sub>I</sub> = 0 V or V <sub>CC</sub>	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, V <sub>CC</sub> = 3.3V, V <sub>I</sub> = 0 V or V <sub>CC</sub>	25	pF

# MC74LCX540

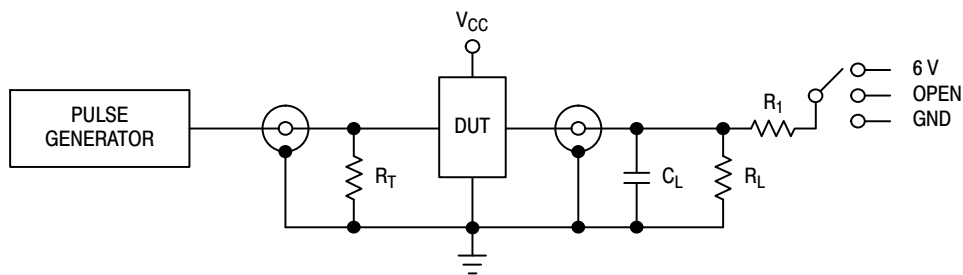


**WAVEFORM 1 - PROPAGATION DELAYS**  
 $t_R = t_F = 2.5 \text{ ns}$ , 10% to 90%;  $f = 1 \text{ MHz}$ ;  $t_W = 500 \text{ ns}$



**WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES**  
 $t_R = t_F = 2.5 \text{ ns}$ , 10% to 90%;  $f = 1 \text{ MHz}$ ;  $t_W = 500 \text{ ns}$

**Figure 3. AC Waveforms**



Test	Switch
$t_{PLH}$ , $t_{PHL}$	Open
$t_{PZL}$ , $t_{PLZ}$	6 V
Open Collector/Drain $t_{PLH}$ and $t_{PHL}$	6 V
$t_{PZH}$ , $t_{PHZ}$	GND

$C_L = 50 \text{ pF}$  or equivalent (Includes jig and probe capacitance)  
 $R_L = R_1 = 500 \text{ } \Omega$  or equivalent  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50 \text{ } \Omega$ )

**Figure 4. Test Circuit**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

SOIC-20 WB  
CASE 751D-05  
ISSUE H

DATE 22 APR 2015

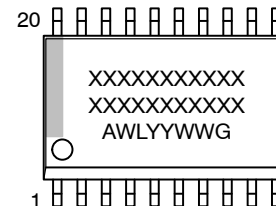


NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

### GENERIC MARKING DIAGRAM\*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

### RECOMMENDED SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98ASB42343B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-20 WB	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



TSSOP-20 WB  
CASE 948E  
ISSUE D

DATE 17 FEB 2016

SCALE 2:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**GENERIC MARKING DIAGRAM\***



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

<b>DOCUMENT NUMBER:</b>	<b>98ASH70169A</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>TSSOP-20 WB</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.